L Number	Hits	Search Text	DB	Time stamp
1	585	(kozo near2 nakamura or toshiaki near2 saishoji or hirotaka near2 nakajima or masashi near2 nishimura or toshirou near2 kotooka near2 yoshiyuki near2 shimanuki).in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/29 11:25
2	35	((kozo near2 nakamura or toshiaki near2 saishoji or hirotaka near2 nakajima or masashi near2 nishimura or toshirou near2 kotooka near2 yoshiyuki near2 shimanuki).in.) and heat near2 treat$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/29 11:25
3	0	((kozo near2 nakamura or toshiaki near2 saishoji or hirotaka near2 nakajima or masashi near2 nishimura or toshirou near2 kotooka near2 yoshiyuki near2 shimanuki).in.) and heat near2 treat$5 and ramp$5 near2 rate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/29 11:26
-	20	"5954873"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/17 13:34
-	17	"5968264"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/17 13:35
-	16	"5788763"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/17 13:58
-	373	czochralski and (temperature adj gradient) and (speed or velocity)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/17 14:00
-	332	czochralski and (temperature adj gradient) same (speed or velocity or rate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/17 14:32
-	606	memc.as.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/17 14:32
-	174	memc.as. and czochralski	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/17 14:41
-	53	memc.as. and czochralski and gradient	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/04 14:43
-	873	wafer and (anneal$3 or (heat adj treat$4) or (rapid adj thermal) or RTA or RTP or PTP) and czochralski	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/17 16:27
-	598	wafer and (anneal$3 or (heat adj treat$4) or (rapid adj thermal) or RTA or RTP or PTP) same temperature and czochralski	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/17 16:30

-	256	(anneal$ or heat$3 near2 treat$) near15 (si or silicon) near2 (wafer or substrate) same temperature near10 ("700" or "800" or "650" or "750" or "900" or "950")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/30 15:42
-	38	(anneal$ or heat$3 near2 treat$) near15 (si or silicon) near2 (wafer or substrate) same temperature near10 ("700" or "800" or "650" or "750" or "900" or "950") same rate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/30 15:47
-	15	(anneal$ or heat$3 near2 treat$) near15 (si or silicon) near2 (wafer or substrate) same temperature same rate near2 less	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/30 15:47
-	248	((Thermal or temperature) adj gradient) near5 (speed or rate) and czochralski	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/05 10:04
-	2	5567399.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/05 10:32
-	251	(thermal or temperature) near2 gradient near5 (speed or rate) and czochralski	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/05 10:34
-	145	(thermal or temperature) near2 gradient near5 pull$3 near3 (speed or rate) and czochralski	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/05 11:08
-	1	9315882.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/05 11:08
-	2	09315882.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/05 11:08
-	5663	heat near2 treat$4 same (si or silicon) near5 (single near2 crystal$5 or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/19 17:05
-	1655	heat near2 treat$4 near10 temperature same (si or silicon) near5 (single near2 crystal$5 or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/19 17:05
-	113	heat near2 treat$4 near10 temperature near10 (ramp$4 or rate) same (si or silicon) near5 (single near2 crystal$5 or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/19 17:43
-	2	"07165495"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/19 17:14
-	182	heat near2 treat$4 near10 temperature near5 low same (si or silicon) near5 (single near2 crystal$5 or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/19 17:49

~	15	heat near2 treat$4 near10 temperature near5 initial$5 same (si or silicon) near5 (single near2 crystal$5 or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/20 09:08
~	17	heat near2 treat$4 near10 temperature near5 start$5 same (si or silicon) near5 (single near2 crystal$5 or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/20 09:23
~	195	(sueoka near2 koji or koike near2 yasuo or sadamitsu near2 shinsuke).in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/20 09:24
~	2	((sueoka near2 koji or koike near2 yasuo or sadamitsu near2 shinsuke).in.) and (start$5 or initial$5 or starting initiat$5) near6 temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/20 09:25
~	26	((sueoka near2 koji or koike near2 yasuo or sadamitsu near2 shinsuke).in.) and temperature same (heat near2 treat$5 or anneal$5) same (si or silicon) near5 (substrate or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/29 11:23